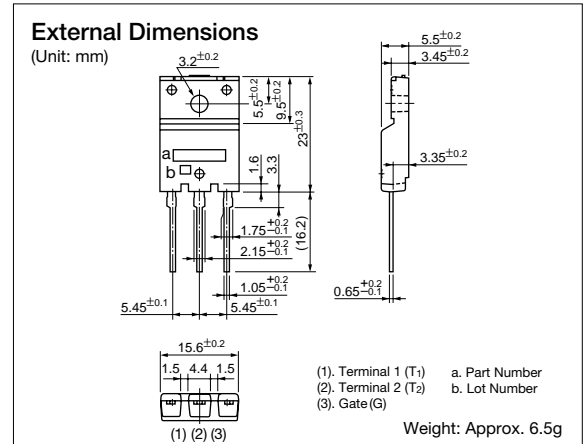


# TO-3PF 12A Triac

# TM1262B-R

## ■ Features

- Repetitive peak off-state voltage:  $V_{DRM}=600V$
- RMS on-state current:  $I_{T(RMS)}=12A$
- Gate trigger current:  $I_{GT}=8mA$  max (MODE I, II, III)
- Isolation voltage:  $V_{ISO}=2000V(AC, 1min.)$
- For resistive load
- UL approved type available



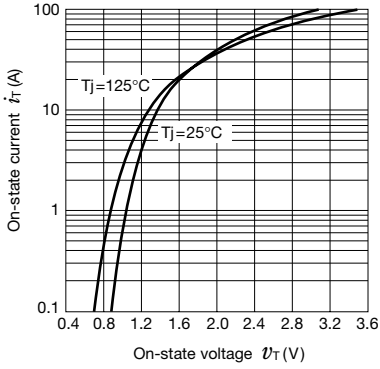
## ■ Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit	Conditions
Repetitive peak off-state voltage	$V_{DRM}$	600	V	$R_{GK}=\infty$ , $T_J=-40^{\circ}C$ to $+125^{\circ}C$
RMS on-state current	$I_{T(RMS)}$	12	A	Conduction angle $360^{\circ}$ , $T_C=98^{\circ}C$
Surge on-state current	$I_{TSM}$	120	A	50Hz full-cycle sine wave, Peak value, Non-repetitive, $T_J=125^{\circ}C$
Peak gate current	$I_{GM}$	2	A	$f \geq 50Hz$ , duty $\leq 10\%$
Peak gate power loss	$P_{GM}$	5	W	$f \geq 50Hz$ , duty $\leq 10\%$
Average gate power loss	$P_{G(AV)}$	0.5	W	
Junction temperature	$T_J$	-40 to +125	$^{\circ}C$	
Storage temperature	$T_{stg}$	-40 to +125	$^{\circ}C$	
Isolation voltage	$V_{ISO}$	2000	Vrms	50Hz Sine wave, RMS, Terminal to Case, 1 min.

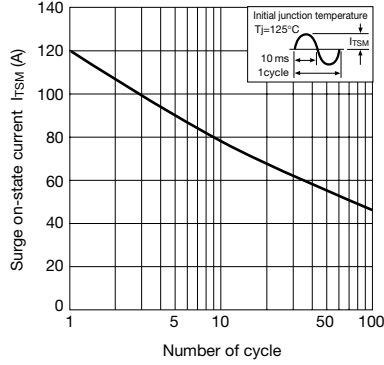
## ■ Electrical Characteristics

Parameter	Symbol	Ratings			Unit	Conditions		
		min	typ	max				
Off-state current	$I_{DRM}$		0.3	2.0	mA	$V_D=V_{DRM}$ , $R_{GK}=\infty$ , $T_J=125^{\circ}C$		
				0.1		$V_D=V_{DRM}$ , $R_{GK}=\infty$ , $T_J=25^{\circ}C$		
On-state voltage	$V_{TM}$			1.6	V	$I_{TM}=16A$ , $T_C=25^{\circ}C$		
Gate trigger voltage	I	$V_{GT}$	0.8	1.1	1.8	V	$V_D=20V$ , $R_L=40\Omega$ , $T_C=25^{\circ}C$	$T_2^+$ , $G^+$
	II		0.4	0.6	1.2			$T_2^+$ , $G^-$
	III		0.4	0.7	1.2			$T_2^-$ , $G^-$
	IV			2.1				$T_2^-$ , $G^+$
Gate trigger current	I	$I_{GT}$	2.0	5.0	8.0	mA	$V_D=20V$ , $R_L=40\Omega$ , $T_C=25^{\circ}C$	$T_2^+$ , $G^+$
	II		2.0	4.5	8.0			$T_2^+$ , $G^-$
	III		2.0	5.0	8.0			$T_2^-$ , $G^-$
	IV			25				$T_2^-$ , $G^+$
Gate non-trigger voltage	$V_{GD}$	0.1			V	$V_D=1/2 \times V_{DRM}$ , $T_J=125^{\circ}C$		
Holding current	$I_H$		6		mA	$T_J=25^{\circ}C$		
Thermal resistance	$R_{th}$			2.0	$^{\circ}C/W$	Junction to case		

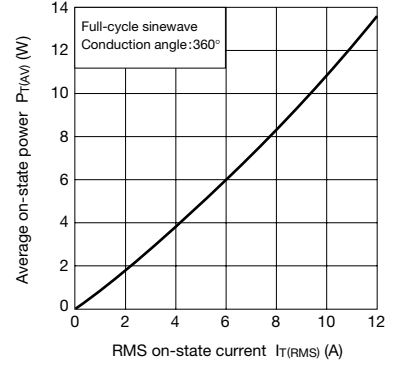
$V_T - I_T$  Characteristics (max)



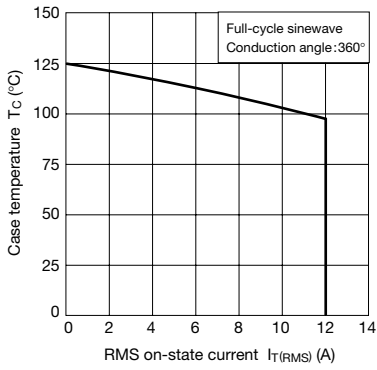
$I_{TSM}$  Ratings



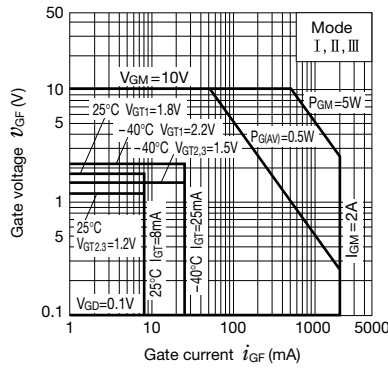
$I_T(RMS) - P_T(AV)$  Characteristics



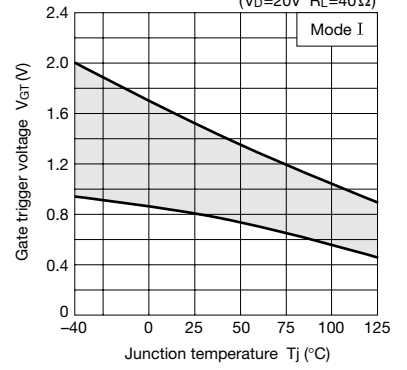
$I_T(RMS) - T_c$  Ratings



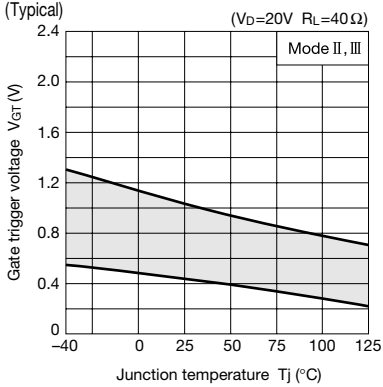
Gate Characteristics



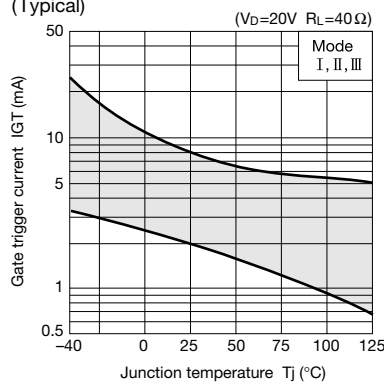
$V_{GT}$  temperature characteristics (Typical)



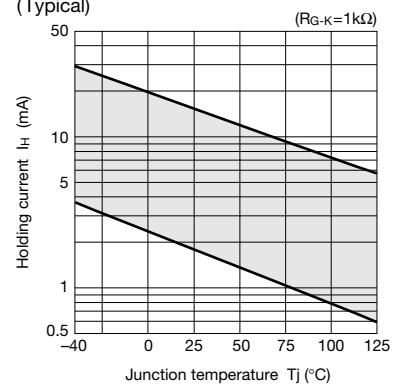
$V_{GT}$  (Mode II, III) temperature characteristics (Typical)



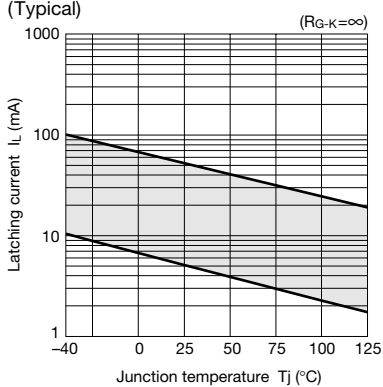
$I_{GT}$  temperature characteristics (Typical)



$I_H$  temperature characteristics (Typical)



$I_L$  temperature characteristics (Typical)



$r_{th(j-c)} - t$  Characteristics

